

Ch.1

Terahertz Time-Domain Spectrometer

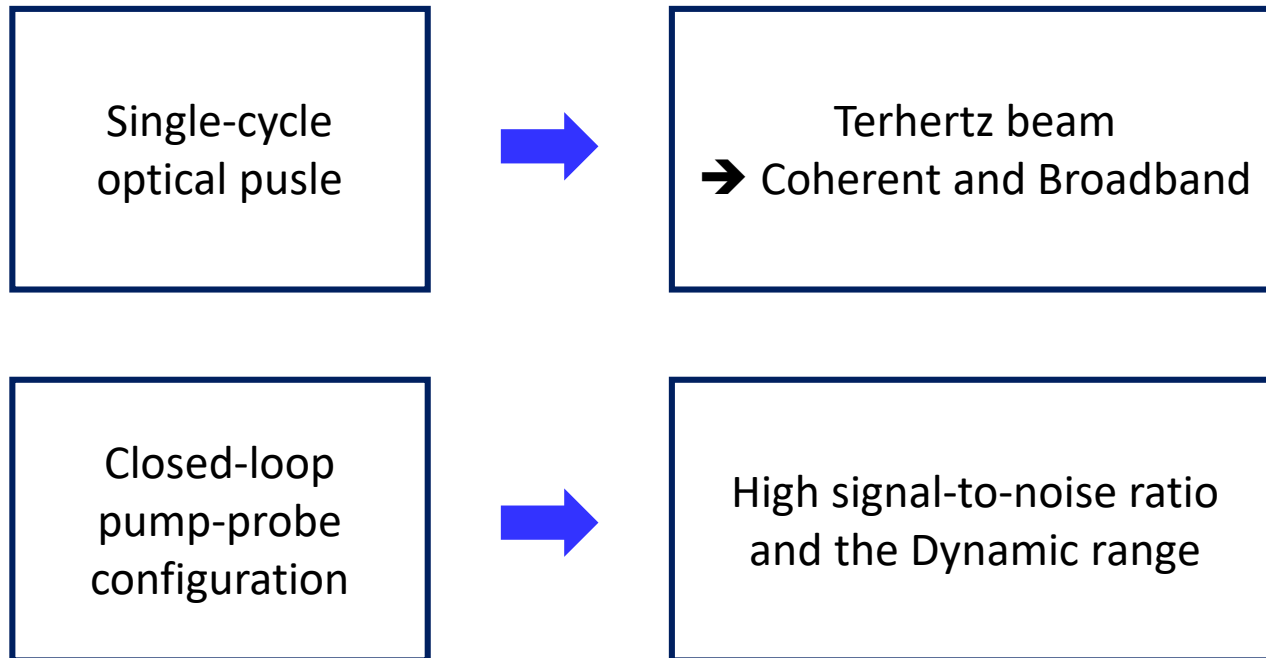
Lee Jong Geon

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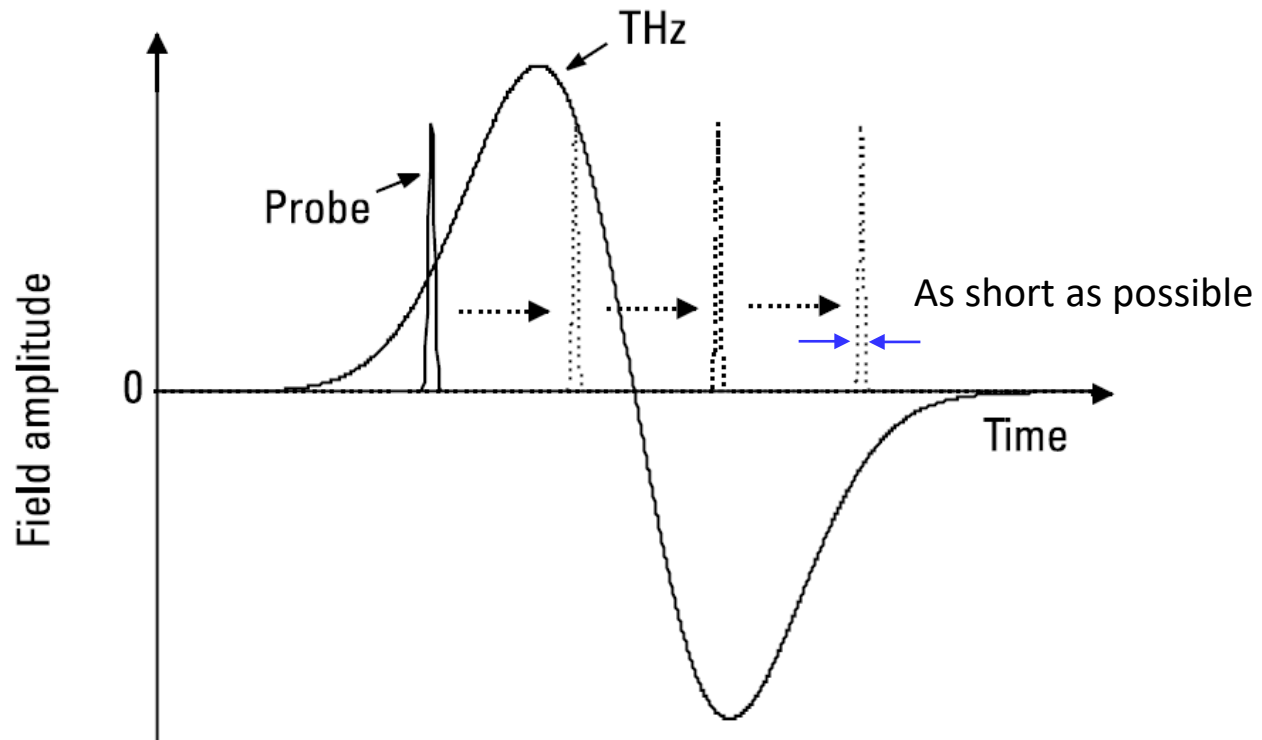
1. Pulsed Terahertz Time-Domain Spectrometers
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Pulsed Terahertz Time-Domain Spectrometers

1.1 Principles of Operation

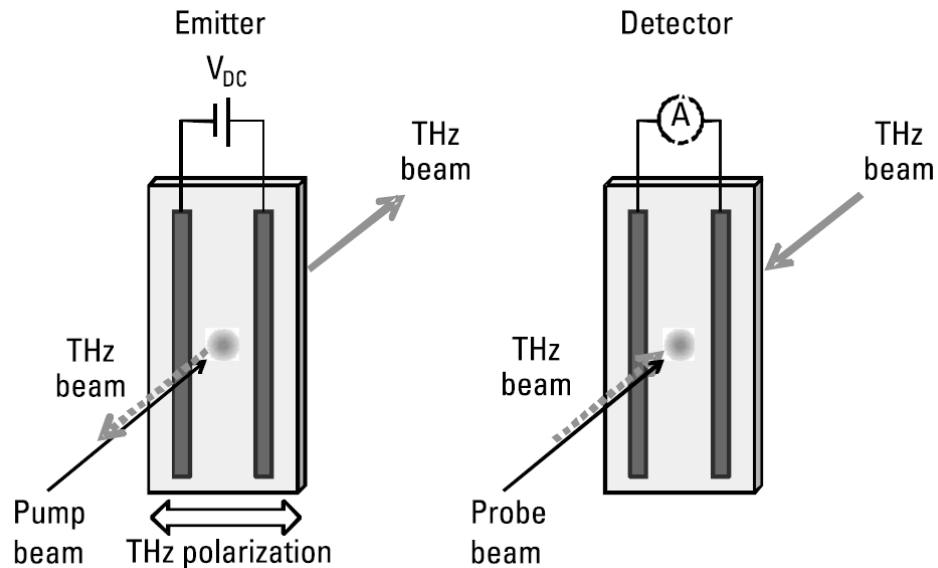


1.1 Principles of Operation



$$Signal(t_0) \propto \int_{-\infty}^{\infty} I_{\text{probe}}(t - t_0) E_{THZ}(t) dt$$

1.2 Photoconductive Emitters and Detectors



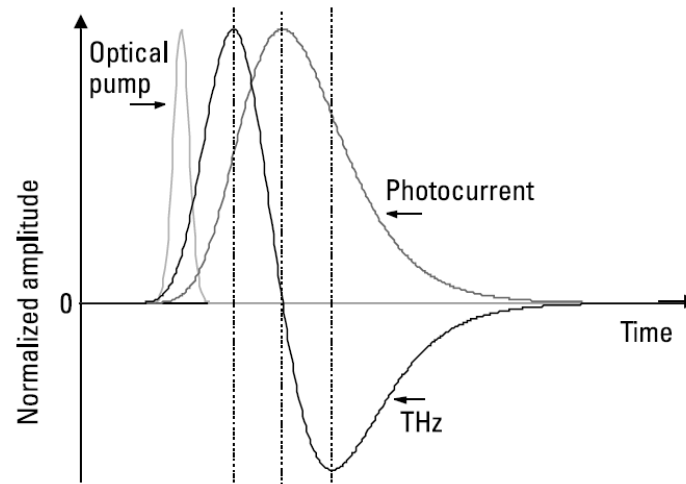
Ti-sapphire (800nm) \rightarrow 1.55eV
GaAs \rightarrow 1.42eV

\rightarrow generate carriers

$$E_{THz}(r, t) = \frac{l_e}{4\pi\epsilon_0 c^2 r} \frac{\partial J(t)}{\partial t} \sin \theta \propto \frac{\partial J(t)}{\partial t}$$

$$J_{PC} = q_C N_C v_C \propto I_{opt} V_{DC}$$

1.2 Photoconductive Emitters and Detectors



- The rise time of the photocurrent: the pump laser pulse length
- The fall time of the photocurrent: 1. the pulse length, 2. the semiconductor carrier lifetime, and 3. the time it takes for carrier to be swept out of the active region by the bias field

Emitter material

Mira

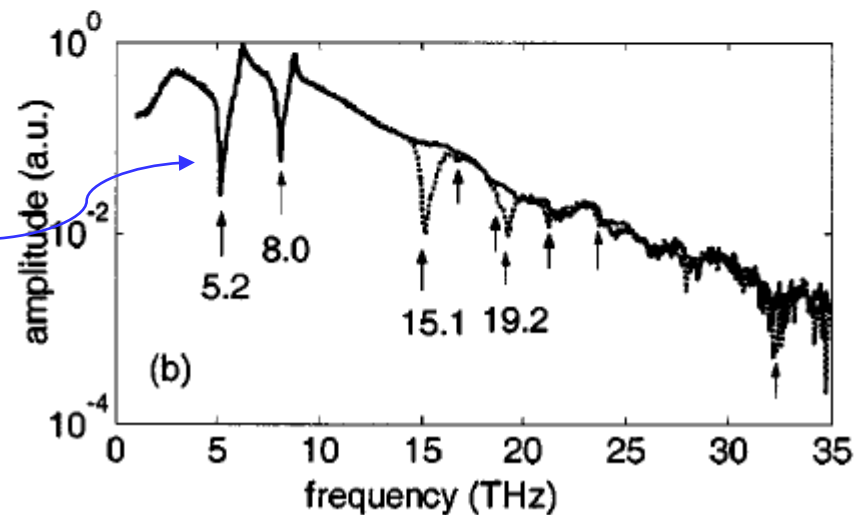
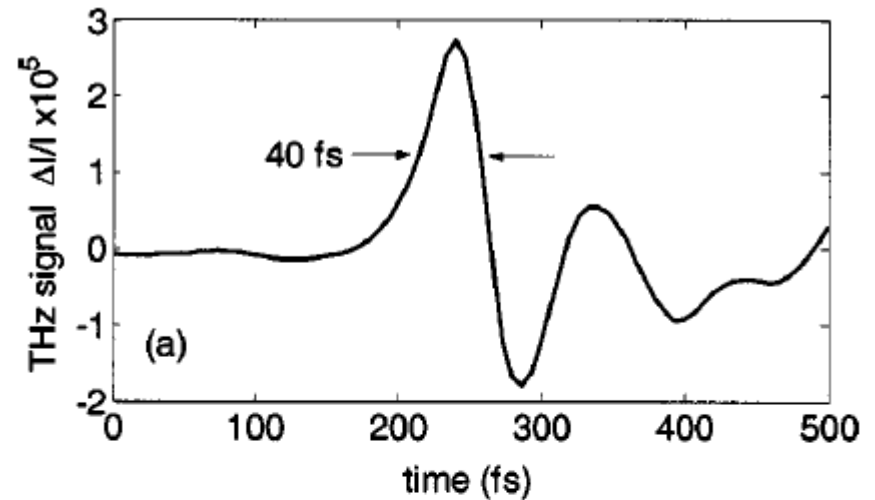
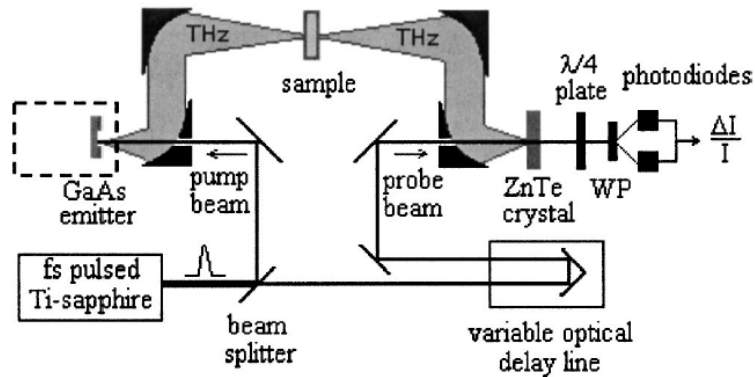
- Large optical absorption coefficient
- High optical damage threshold
- High breakdown voltage

Sakai

- Subpicosecond carrier lifetime
- Relatively high carrier mobility
- High breakdown fields

$$J_{THz}(t_0) = \int_{-\infty}^{t_0} \sigma_{PC}(t_0 - t) E_{THz}(t) dt$$

1.2 Photoconductive Emitters and Detectors



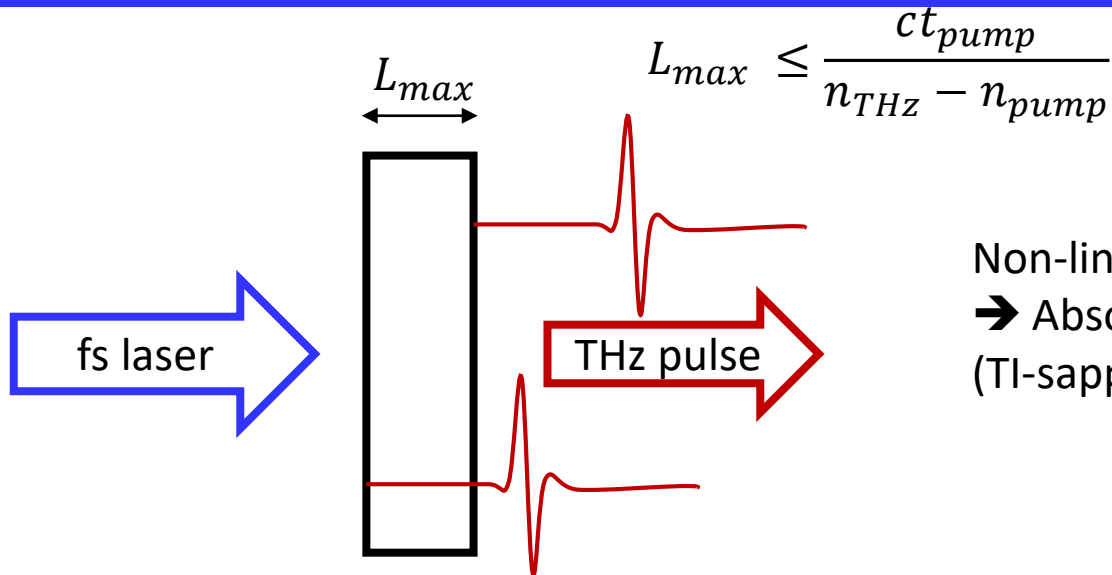
ZnTe detector

→ (TO phonon energy: 22 meV = 5.3THz)

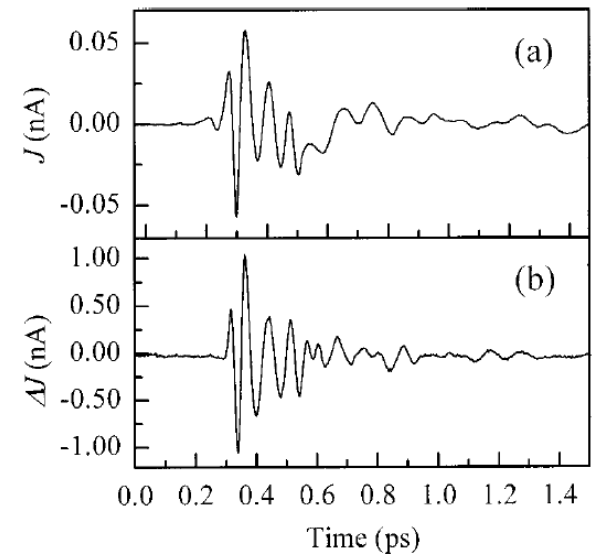
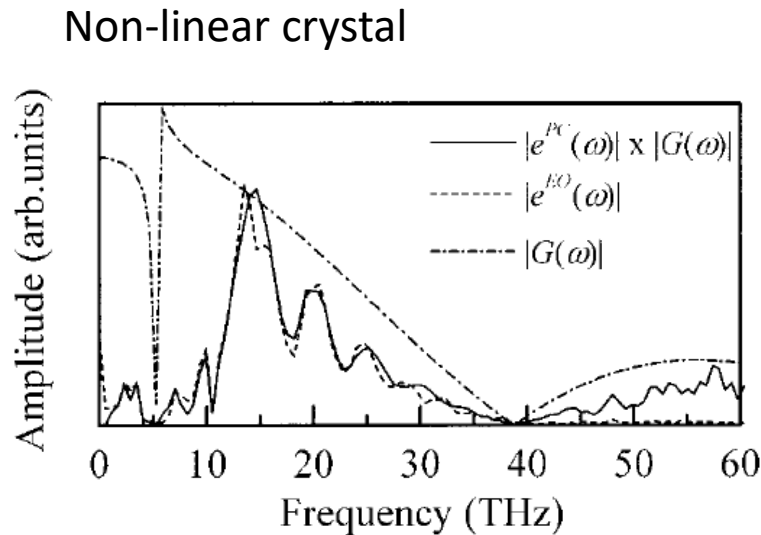
LT-GaAs

→ (TO phonon energy: 33 meV = 8.0THz)

1.3 Optical Rectification

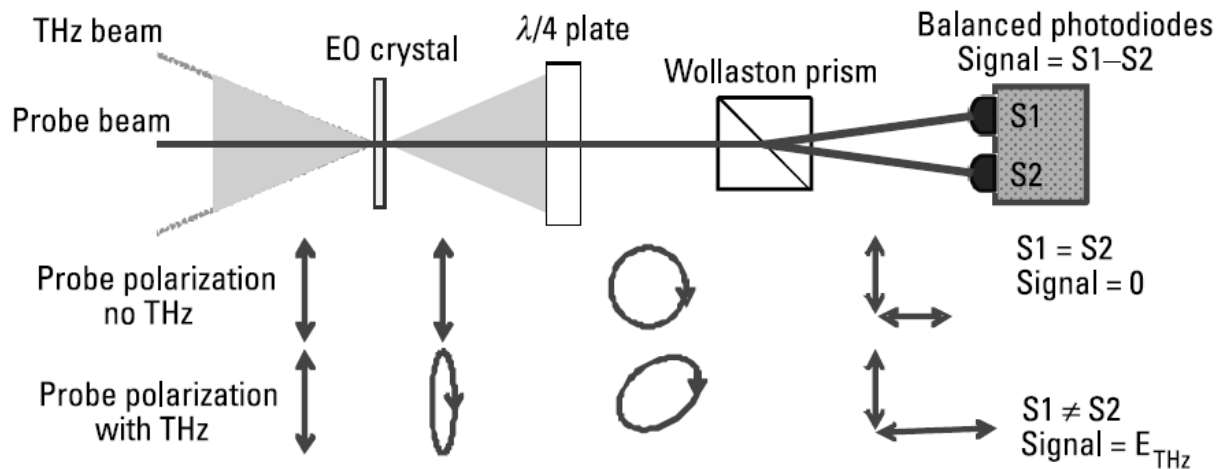


Non-linear crystal: ZnTe crystal
 → Absorption (phonon): 5.3, 3.5, 1.5 THz
 (Ti-sapphire, 800nm)



1.4 Electro-Optic Detection

Electro-optic detection relies on the **Pockels effect** where an electric field gives rise to birefringence in an optical material.



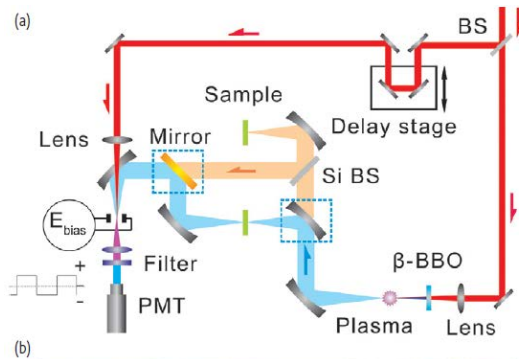
$$\frac{\Delta I}{I} = \frac{1}{2}(1 + \sin \Delta\varphi) - \frac{1}{2}(1 - \sin \Delta\varphi) = \sin \Delta\varphi \approx \Delta\varphi \quad \Delta\varphi = \frac{2\pi L}{\lambda_{\text{probe}}} n_{\text{probe}}^3 r_{\text{eff}} E_{\text{THz}}$$

Advantages

- Easier alignment, lower sensitivity to probe beam pointing
- No need microfabricated highly specialized semiconductor device
- Simpler electronics

1.5 Terahertz Air-Based Coherent Detection

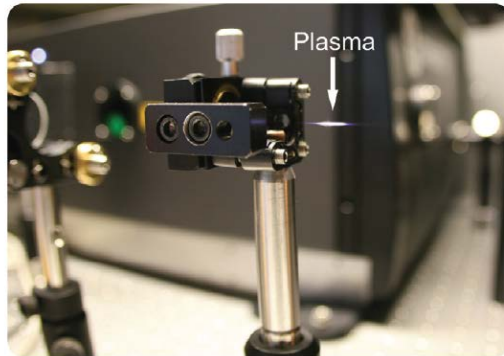
Terahertz air-based coherent detection (THz-ABCD) uses **ionized air** as a medium for ultra-broadband terahertz generation and detection



$$E_{THz} \propto \chi^{(3)} E_{\omega}^2 E_{2\omega}$$

$$I_{2\omega}(t_0) \propto 2[\chi^{(3)} E_{\omega}^2(t)]^2 E_{bias} E_{THz}(t - t_0)$$

➔ 3-order optical nonlinearity in plasma



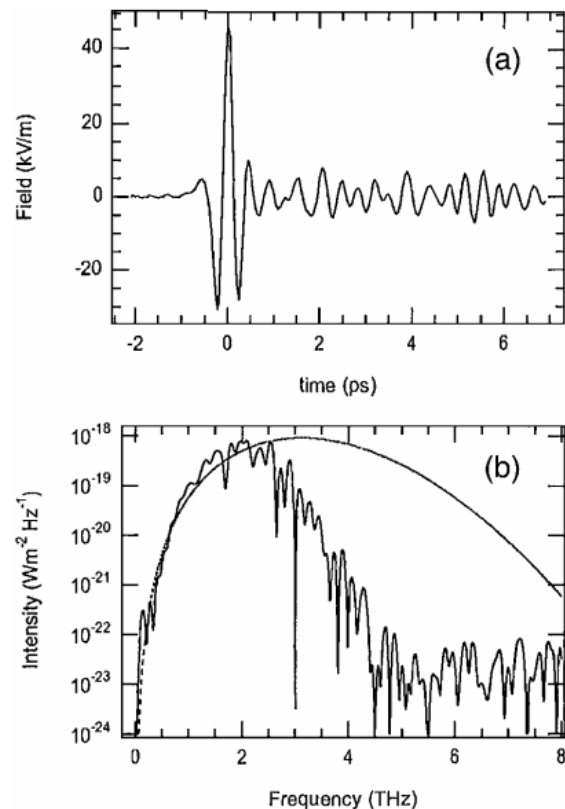
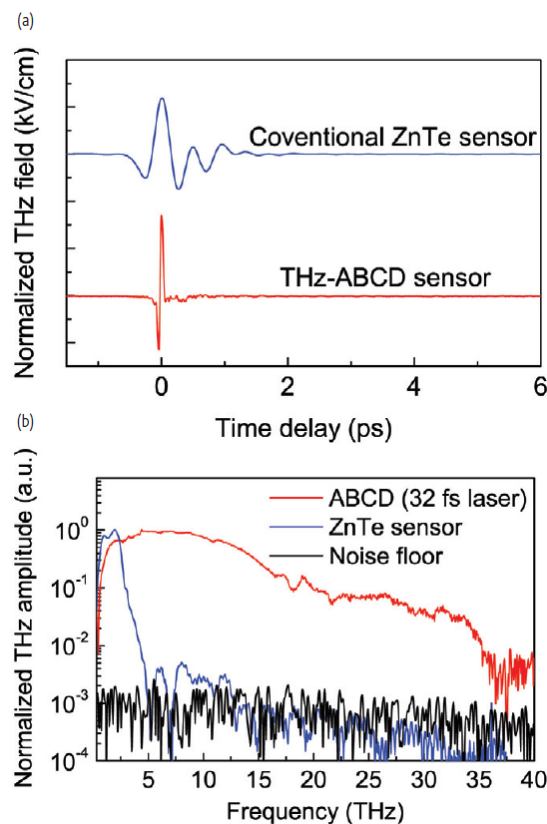
Ti-sapphire (65 fs, 800 nm)

Four-Wave Rectification (FWR) method

➔ β -BBO lens focuse 150 μ J of energy

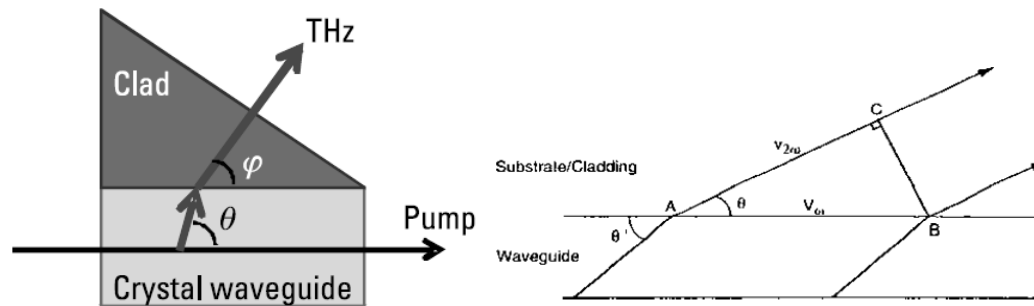
➔ The peak optical intensity: 5×10^{14} W/cm²

1.5 Terahertz Air-Based Coherent Detection



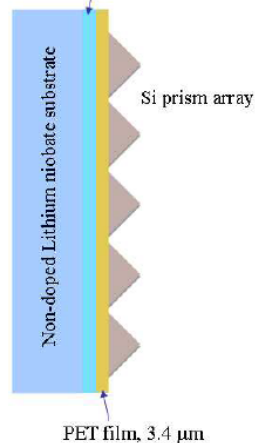
The requirement for an amplified ultrafast laser as a pump source and issues arising from working with plasma

1.6 Cherenkov Emitters and Detectors

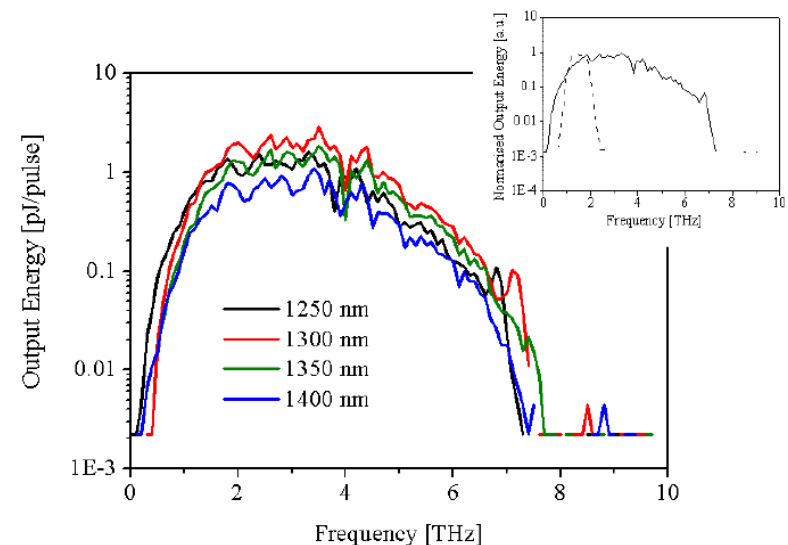
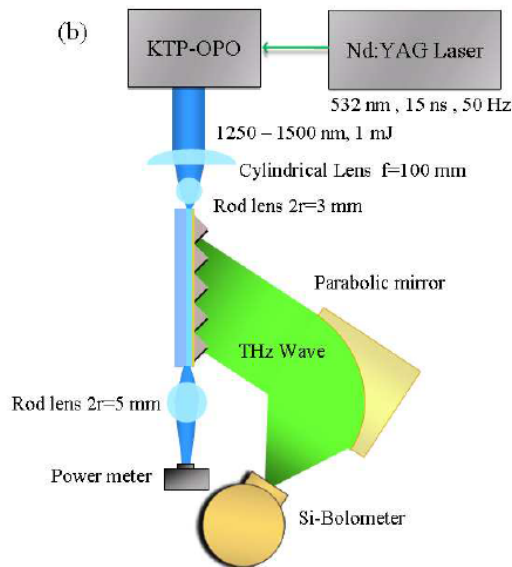


$$\cos \theta = \frac{V_{\omega}}{v_{2\omega}} = \frac{n_{\text{pump}}}{n_{\text{THz}}}$$

(a) 5 mol % MgO-doped Lithium niobate Waveguide, 3.8 μm

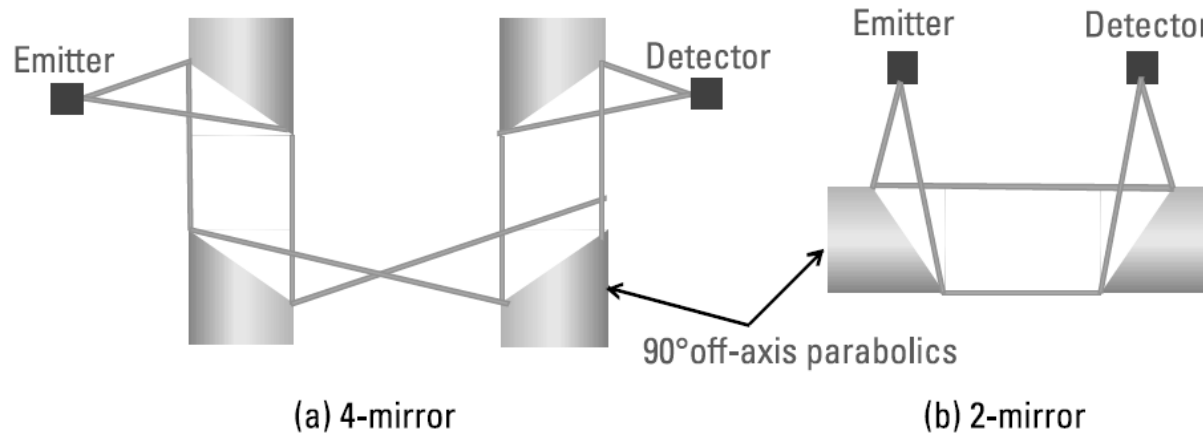


(b)



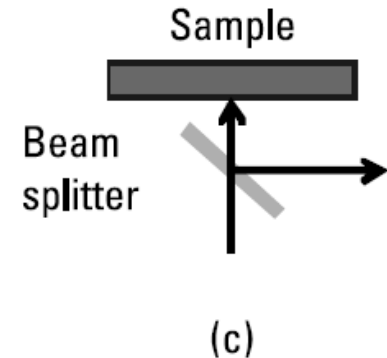
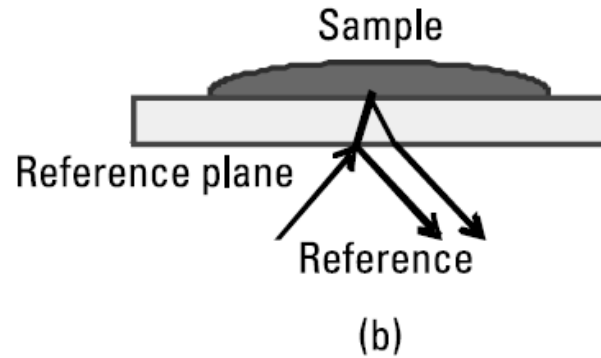
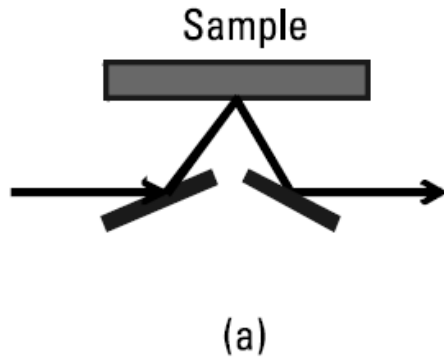
Time-Domain Spectrometer Configurations

2.1 Transmission



- The great majority of Terhertz TDS system
➔ A more accurate and precise measure of attenuation and phase shift
- Using off-axis parabolic mirrors

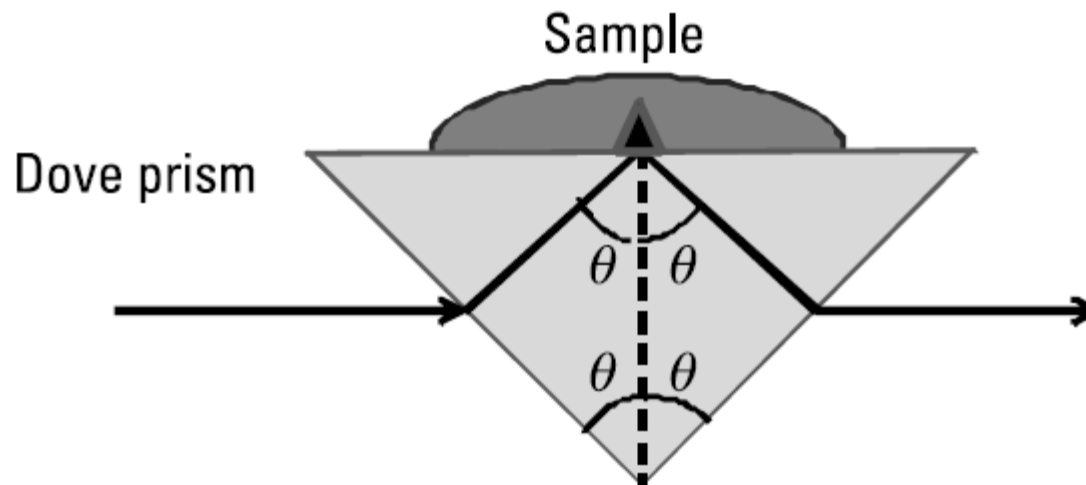
2.2 Reflection



- Opaque materials (a)
- Liquid materials (b) → need great care to avoid air gaps
- Normal incidence (c) → the incurred loss of terahertz power is at least 75%

2.3 Attenuated Total Reflection

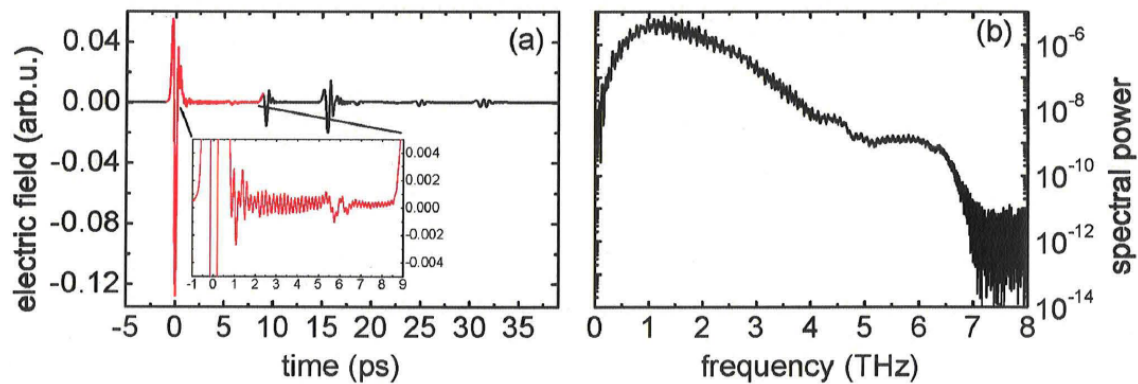
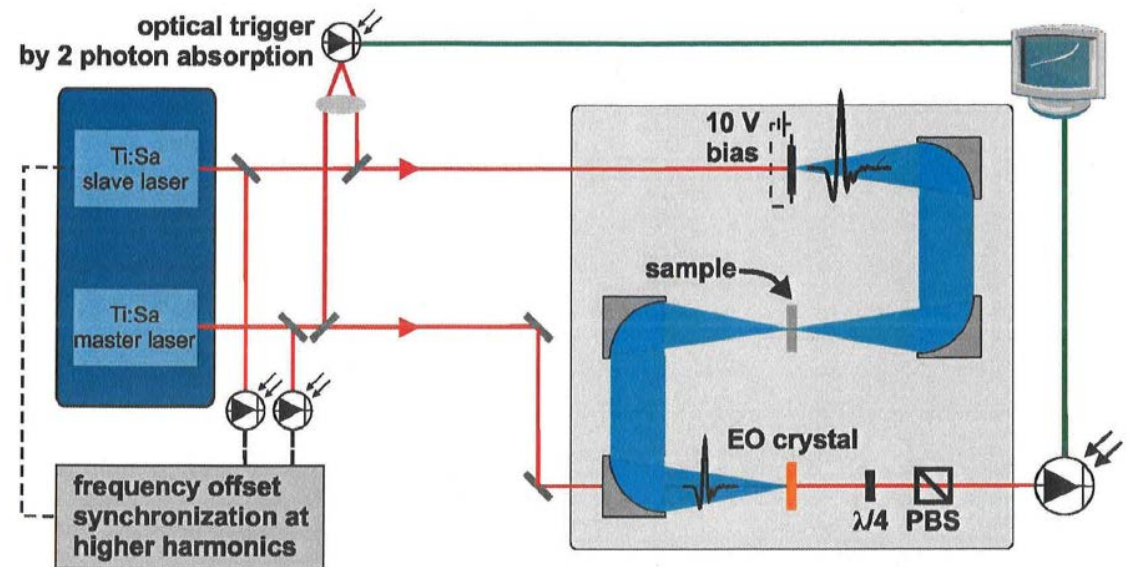
Attenuated Total Reflection (ATR) relies on total internal reflection at an interface, which is modified (attenuated) by the interaction of the **evanescent wave** with the material of the sample



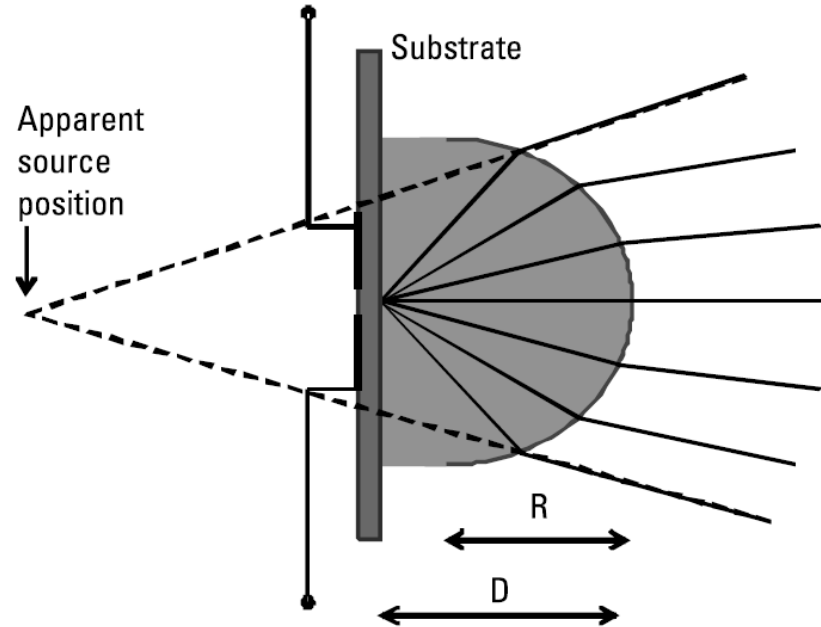
$$\sin \theta = n_{\text{prism}} \sin \left(2\theta - \frac{\pi}{2} \right)$$

$$d_{\text{evanescent}}(\lambda) = \lambda \frac{n_{\text{prism}}^2 n_{\text{sample}} \cos \theta}{\pi (n_{\text{prism}}^2 - n_{\text{sample}}^2) (n_{\text{prism}}^2 \sin^2 \theta - n_{\text{sample}}^2)^{1/2}}$$

2.4 Asynchronous Optical Sampling



2.5 Substrate Lenses



$$D = R \left(\frac{n + 1}{n} \right)$$

References

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